



MMDT8050S

NPN EPITAXIAL SILICON TRANSISTOR

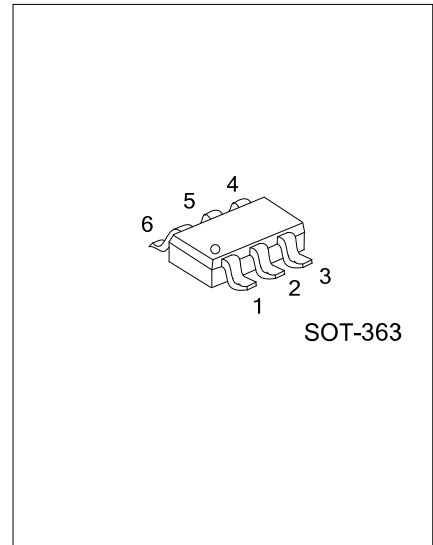
LOW V_{CE(sat)} NPN EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

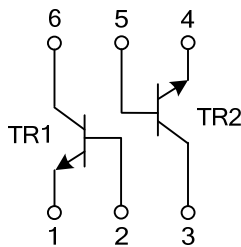
The UTC **MMDT8050S** is a Dual NPN epitaxial planar transistor. It has low $V_{CE(sat)}$ performance, and the transistor elements are independent, eliminating interference.

FEATURES

- * Low $V_{CE(sat)}$, $V_{CE(sat)} = 40\text{mV (typ.) @ } I_C / I_B = 50\text{mA} / 2.5\text{mA}$
- * Transistor elements are independent, eliminating interference.
- * Mounting cost and area can be cut in half.



EQUIVALENT CIRCUIT

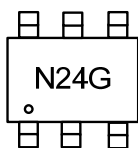


ORDERING INFORMATION

Ordering Number	Package	Pin Assignment						Packing
		1	2	3	4	5	6	
MMDT8050SG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel

<p>MMDT8050SG-AL6-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Green Package 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free and Lead Free
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MARKING



MMDT8050S

NPN EPITAXIAL SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	700	mA
Collector Current (Pulse)	I_{CP}	1.5 (Note 2)	A
Power Dissipation	P_D	200 (total)	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Single pulse, $P_W=10\text{ms}$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100\mu\text{A}, I_E = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1\text{mA}, I_B = 0$	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 30\text{V}, I_E = 0$			1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			100	nA
DC Current Gain(note)	h_{FE1}	$V_{CE} = 1\text{V}, I_C = 1\text{mA}$	100		400	
	h_{FE2}	$V_{CE} = 1\text{V}, I_C = 150\text{mA}$	120			
	h_{FE3}	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.2	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$V_{CE} = 1\text{V}, I_C = 10\text{mA}$			1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	100			MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		9.0		pF

Note: Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

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